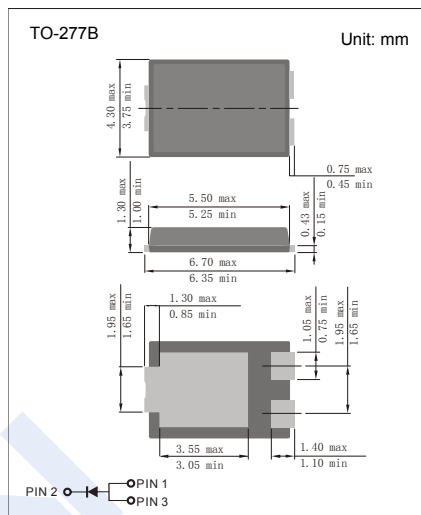


Schottky Diodes

KBR15L60SP5

■ Features

- Low Forward Voltage Drop
- Excellent High Temperature Stability
- Trench Schottky Design using 8" Advanced Technology
- Lead Free Finish, RoHS Compliant
- Excellent ESD protection up to 30KV.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Peak Reverse Voltage	V_{RRM}	60	V
Working Peak Reverse Voltage	V_{RWM}	60	
DC Blocking Voltage	V_R	60	
Average Forward Rectified Current	I_{FAV}	15	A
Peak Forward Surge Current @ 60Hz	I_{FSM}	300	
Thermal Resistance Junction to Case	$R_{\theta JC}$	13	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-65 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

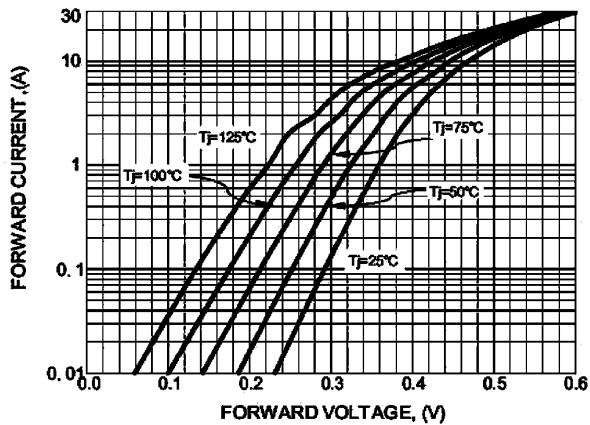
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 0.5 \text{ mA}$	60			V
Forward voltage	V_{F1}	$I_F = 3 \text{ A}, T_J = 25^\circ\text{C}$			0.5	
	V_{F2}	$I_F = 3 \text{ A}, T_J = 125^\circ\text{C}$		0.28		
	V_{F3}	$I_F = 15 \text{ A}, T_J = 25^\circ\text{C}$			0.54	
	V_{F4}	$I_F = 15 \text{ A}, T_J = 125^\circ\text{C}$		0.44		
Reverse voltage leakage current	I_{R1}	$V_R = 60 \text{ V}, T_J = 25^\circ\text{C}$			50	μA
	I_{R2}	$V_R = 60 \text{ V}, T_J = 125^\circ\text{C}$		12		mA

Schottky Diodes

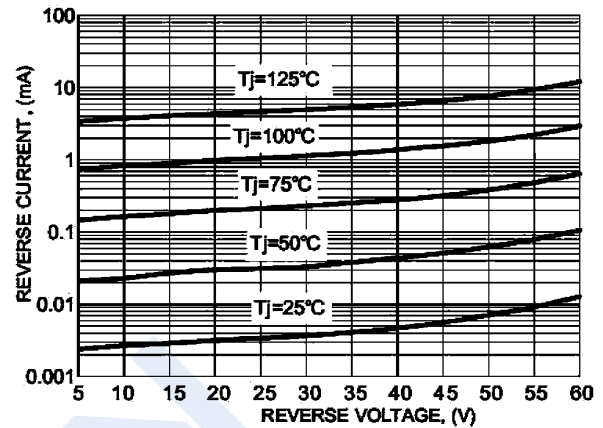
KBR15L60SP5

■ Typical Characteristics

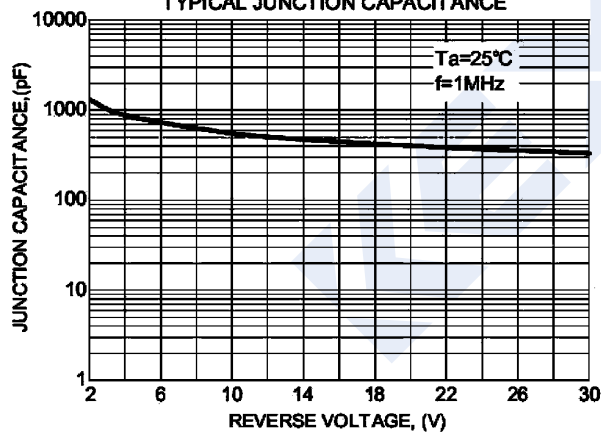
TYPICAL FORWARD CHARACTERISTICS



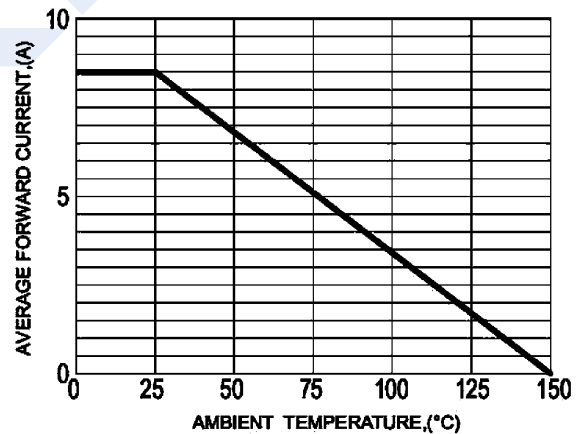
TYPICAL REVERSE LEAKAGE CHARACTERISTICS



TYPICAL JUNCTION CAPACITANCE



TYPICAL FORWARD CURRENT DERATING CURVE



MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

